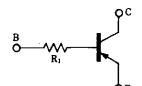


COMPOUND TRANSISTOR BN1A4Z

on-chip resistor PNP silicon epitaxial transistor For mid-speed switching

FEATURES

 On-chip bias resistor (R₁ = 10 kΩ)



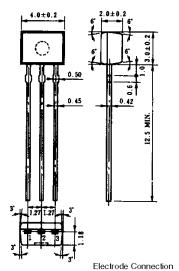
· Complementary transistor with BA1A3Q

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	Vcво	-60	V
Collector to emitter voltage	Vceo	–50	V
Emitter to base voltage	V _{EBO}	- 5	V
Collector current (DC)	Ic(DC)	-100	mA
Collector current (Pulse)	Ic(pulse) *	-200	mA
Total power dissipation	Рт	250	mW
Junction temperature	Tj	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

^{*} PW \leq 10 ms, duty cycle \leq 50 %

PACKAGE DRAWING (UNIT: mm)



ectrode Connection

- 1. Emitter
- Collector
 Base

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	$V_{CB} = -50 \text{ V}, I_E = 0$			100	nA
DC current gain	h _{FE1} **	$V_{CE} = -5.0 \text{ V}, \text{ Ic} = -5.0 \text{ mA}$	135	190	600	-
DC current gain	h _{FE2} **	$V_{CE} = -5.0 \text{ V}, \text{ Ic} = -50 \text{ mA}$	100	170		-
Collector saturation voltage	VCE(sat) **	$I_{\text{C}} = -5.0 \text{ mA}, I_{\text{B}} = -0.25 \text{ mA}$		-0.07	-0.2	V
Low level input voltage	VIL **	$V_{CE} = -5.0 \text{ V}, \text{ Ic} = -100 \ \mu\text{A}$		-0.57	-0.5	V
High level input voltage	V _{IH} **	$V_{CE} = -0.2 \text{ V}, \text{ Ic} = -5.0 \text{ mA}$	-2.0	-0.9		V
Input resistance	R ₁		7.0	10	13.0	kΩ
Turn-on time	ton	V cc = -5.0 V, R L = 1.0 k Ω			0.2	μs
Storage time	t stg	$V_1 = -5.0 \text{ V}, \text{ PW} = 2.0 \ \mu\text{s}$			5.0	μs
Turn-off time	toff	duty cycle≤2 %			6.0	μs

^{**} Pulse test PW \leq 350 μ s, duty cycle \leq 2 %

hfe CLASSIFICATION

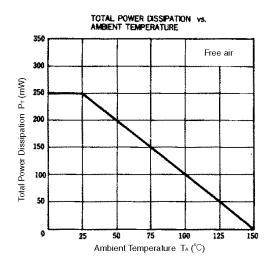
Marking	Q	Р	К
h _{FE1}	135 to 270	200 to 400	300 to 600

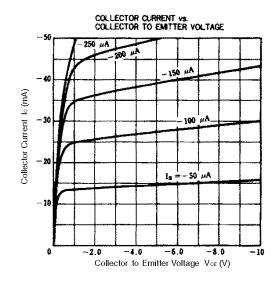
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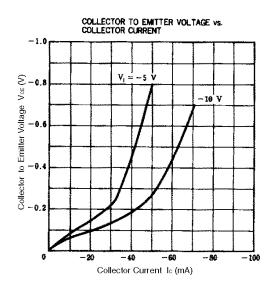
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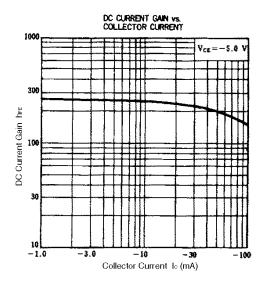


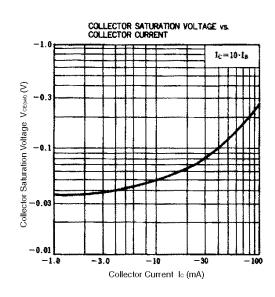
TYPICAL CHARACTERISTICS (Ta = 25°C)

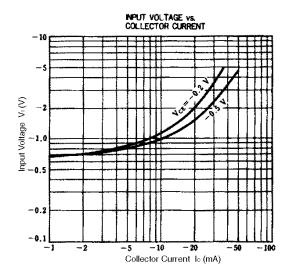


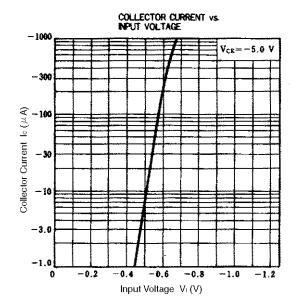


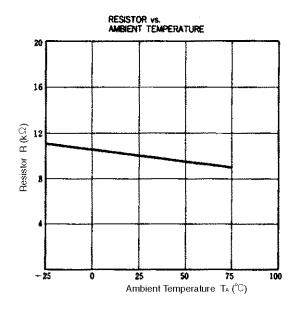












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